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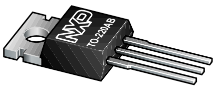

PSMN4R8-100PSE

N-channel 100 V 5 mΩ standard level MOSFET with improved SOA in TO220 package

11 July 2014 Product data sheet

1. General description

Standard level N-channel MOSFET with improved SOA in a TO220 package. Part of NXP's "NextPower Live" portfolio, the PSMN4R8-100PSE is robust enough to withstand substantial in-rush and fault condition currents during turn on/off, whilst offering a low $R_{DS(on)}$ characteristic to keep temperatures down and efficiency up in continued use. Ideal for telecommunication systems based on 48 V backplanes / supply rails.

2. Features and benefits

- Enhanced safe operating area (SOA) for superior protection during linear mode operation
- Very low $R_{DS(on)}$ for low conduction losses

3. Applications

- Electronic fuse
- Hot-swap / Soft-start
- Uninterruptible power supplies
- Motor control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	-	100	V
I_{DM}	peak drain current	pulsed; T_{mb} = 25 °C; $t_p \leq 10$ µs; Fig. 3	-	-	693	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1	-	-	405	W
Static characteristics						
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 12	-	4.3	5	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 50 V; Fig. 14; Fig. 15	-	59	83	nC
$Q_{G(tot)}$	total gate charge		-	196	278	nC

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Datasheet of PSMN4R8-100PSEQ - MOSFET N-CH 100V D2PAK
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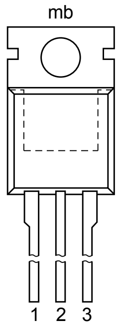
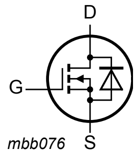
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; unclamped; Fig. 4		-	-	542	mJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 **TO-220AB (SOT78)**	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R8-100PSE	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R8-100PSE	PSMN4R8-100PSE

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j ≥ 25 °C; T_j ≤ 175 °C		-	100	V

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Symbol	Parameter	Conditions		Min	Max	Unit
V_{DGR}	drain-gate voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C; $R_{GS} = 20$ kΩ		-	100	V
V_{GS}	gate-source voltage			-20	20	V
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; Fig. 1		-	405	W
I_D	drain current	$V_{GS} = 10$ V; $T_j = 25$ °C; Fig. 2	[1]	-	120	A
		$V_{GS} = 10$ V; $T_{mb} = 100$ °C; Fig. 2	[1]	-	120	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C; Fig. 3		-	693	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25$ °C	[1]	-	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C		-	693	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 120$ A; $V_{sup} \leq 100$ V; $R_{GS} = 50$ Ω; unclamped; Fig. 4		-	542	mJ

[1] Continuous current limited by package.

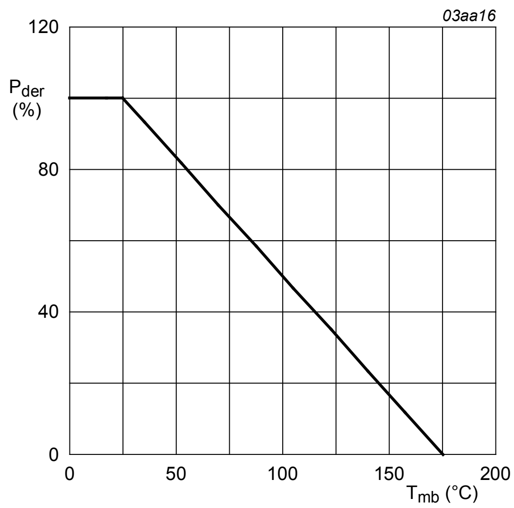
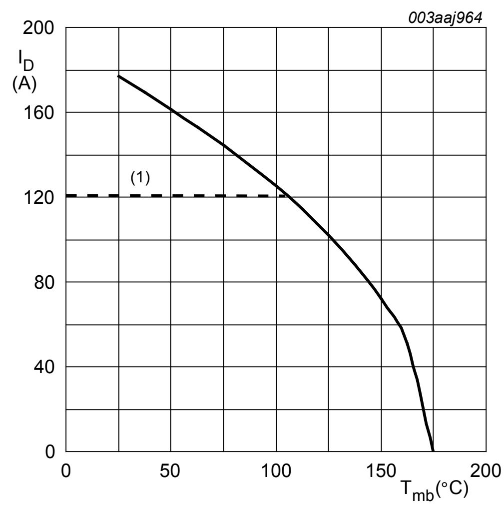


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\,\%$$



(1) Capped at 120A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

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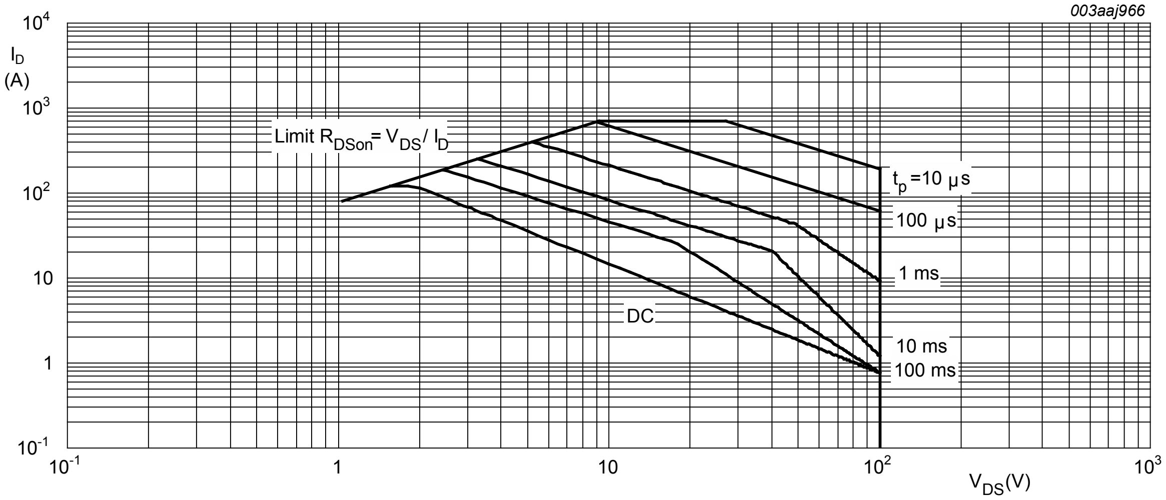

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25$ °C; I_{DM} is a single pulse; Capped at 120 A due to package

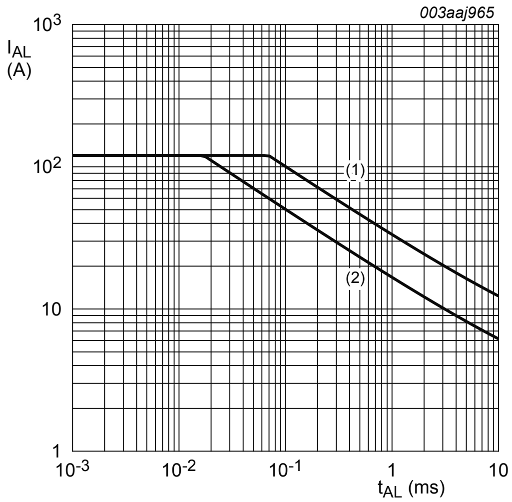

Fig. 4. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 100°C$

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	0.3	0.37	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board		-	60	-	K/W

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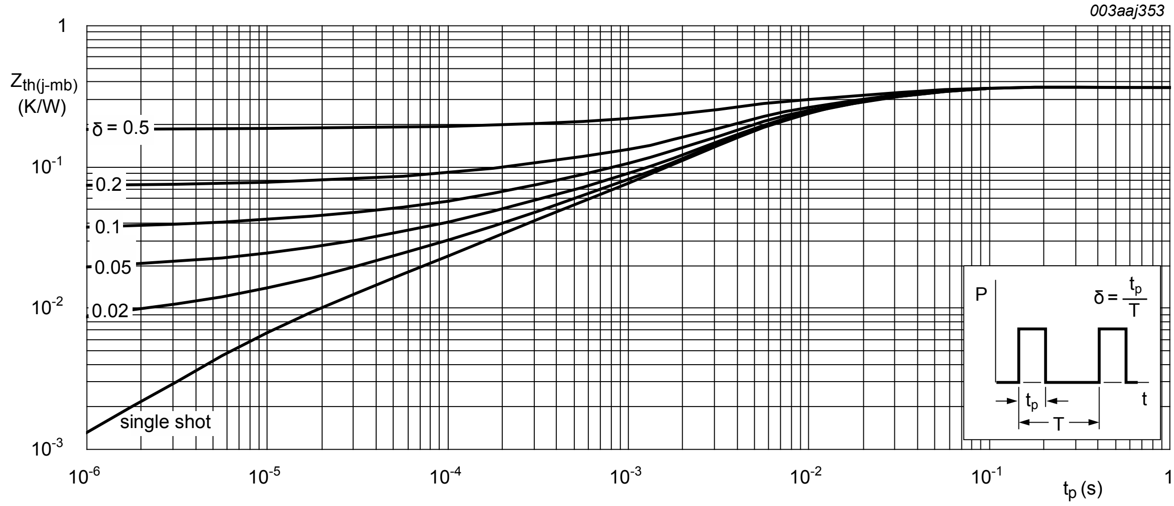

Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		100	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 10; Fig. 11		2	3	4	V
V_{GSth}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 11		1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 11		-	-	4.6	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C		-	0.16	10	µA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 12		-	4.3	5	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; Fig. 13; Fig. 12		-	-	9	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 12; Fig. 13		-	-	13.5	mΩ
R_G	gate resistance	f = 1 MHz		0.43	0.85	1.7	Ω

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 50 V; V_{GS} = 10 V; Fig. 14; Fig. 15		-	196	278	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V		-	166.9	234	nC
Q_{GS}	gate-source charge	I_D = 25 A; V_{DS} = 50 V; V_{GS} = 10 V; Fig. 14; Fig. 15		-	40	56	nC
Q_{GD}	gate-drain charge			-	59	83	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 25 A; V_{DS} = 50 V; Fig. 14; Fig. 15		-	4.3	-	V
C_{iss}	input capacitance	V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 16		-	10665	14400	pF
C_{oss}	output capacitance			-	674	910	pF
C_{rss}	reverse transfer capacitance			-	459	643	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 50 V; R_L = 2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 4.7 Ω		-	41	61.5	ns
t_r	rise time			-	65	97.5	ns
$t_{d(off)}$	turn-off delay time			-	127	190.5	ns
t_f	fall time			-	69	103.5	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 17		-	0.79	1.2	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 50 V		-	72	94	ns
Q_r	recovered charge			-	227	296	nC

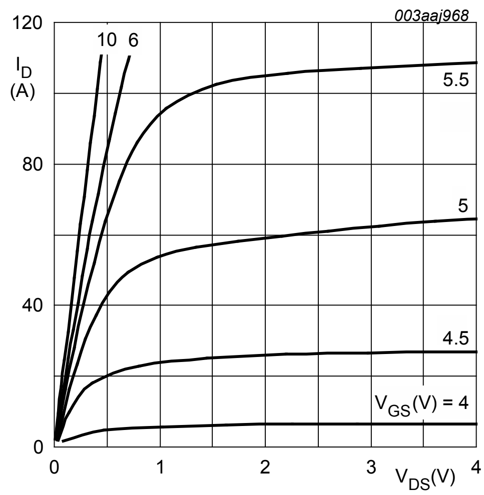

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

$T_j = 25°C$

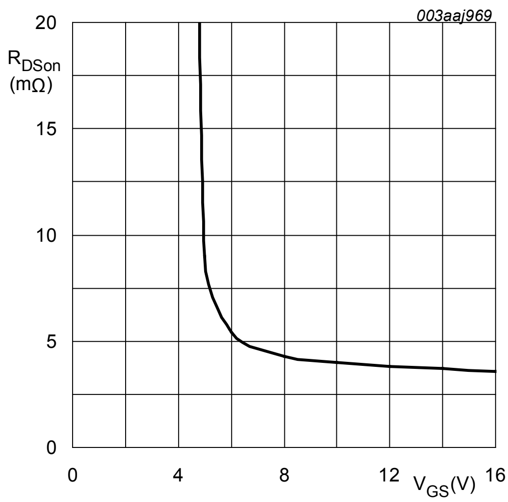

Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25°C;\ I_D = 25A$

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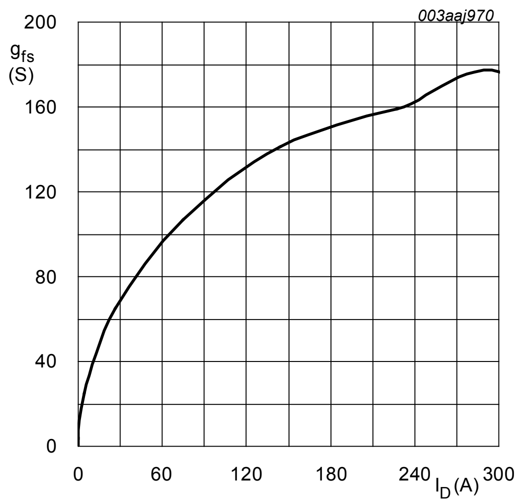

Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25°C;\ V_{DS} = 10V$

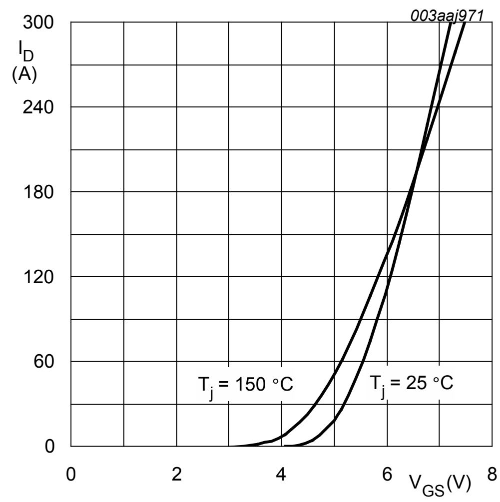

Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

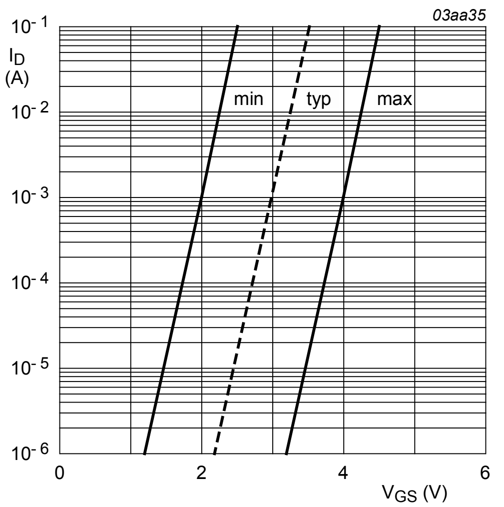

Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25°C; V_{DS} = 5V$

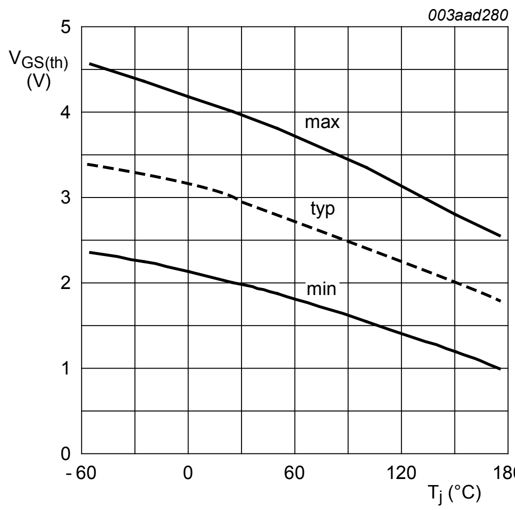

Fig. 11. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\ \text{mA};\ V_{DS} = V_{GS}$

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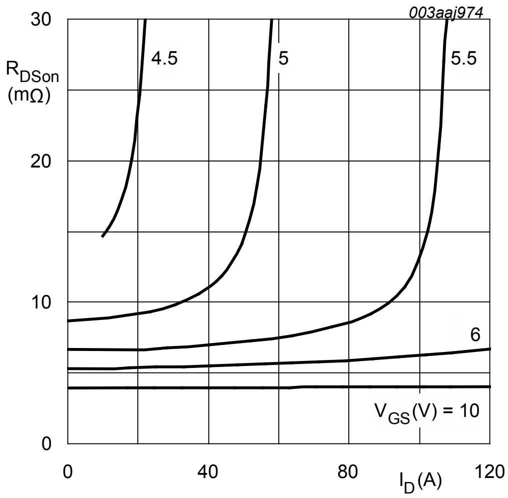

Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25°C$

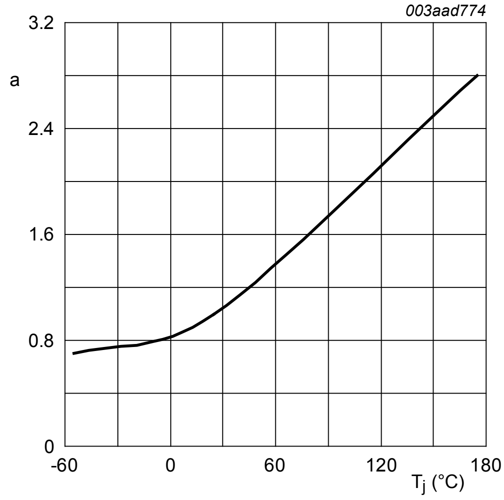

Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25\,°C)}}$$

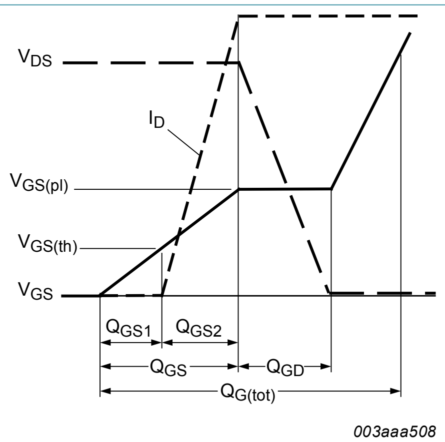

Fig. 14. Gate charge waveform definitions

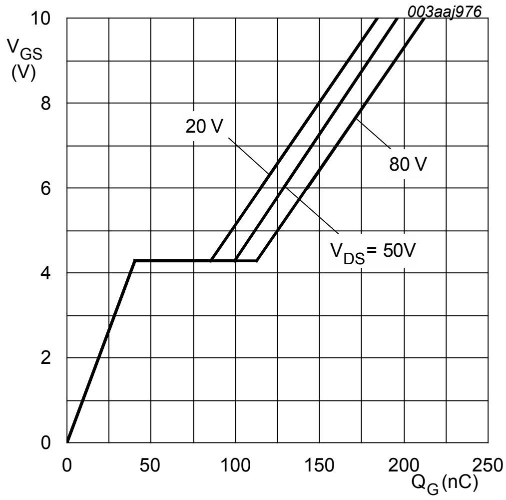

Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25°C;\ I_D = 25 A$

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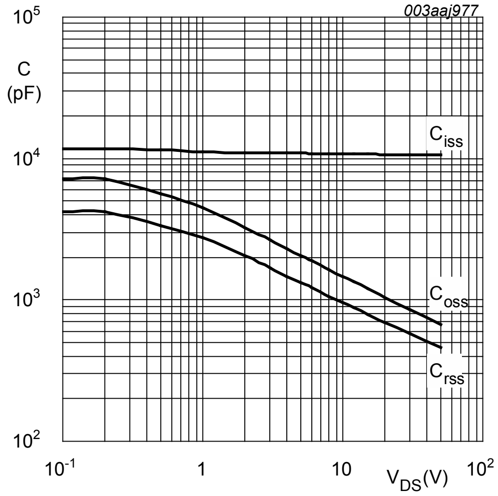

Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0 V;\ f = 1 MHz$

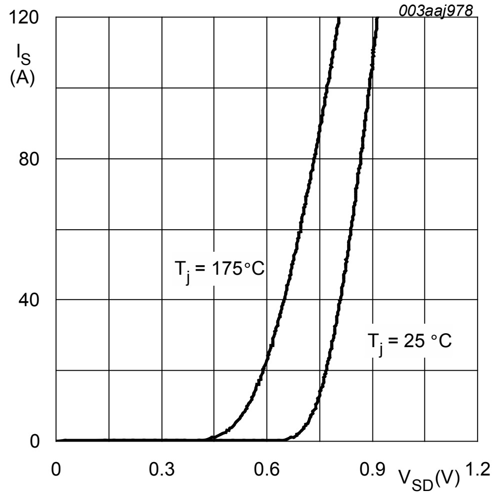

Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0 V$

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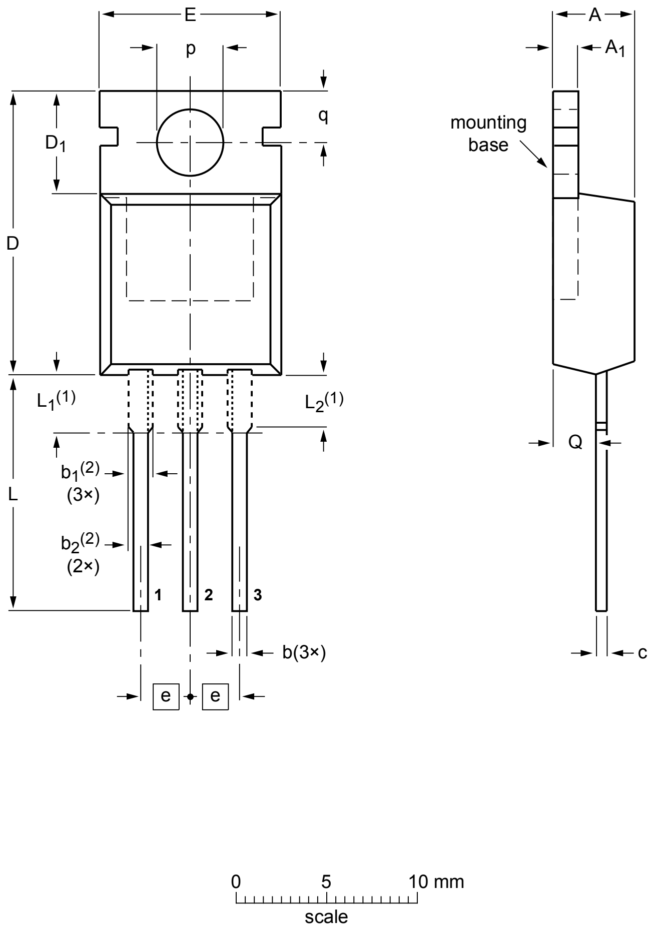
11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1(2)	b_2(2)	c	D	D_1	E	e	L	L_1(1)	L_2(1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Fig. 18. Package outline TO-220AB (SOT78)

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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